POSTER SESSION II, TUESDAY, JULY 23

Session S2 - Semiconductor Single Crystals and Films

S2.01 Improvement of Crystallinity in SiC films prepared by CVD using polysilaethylene
Hiroki Sato (Tohoku University, Japan)

S2.02 Formation of GaN nanorods on vertex of GaN stripes by MOVPE
Dong Ho Lee (National Korea Maritime and Ocean University, South Korea)

S2.03 Crystal Quality and Phase Transition Characteristics of Ga_2O_3 Thin Films Deposited on 4H-SiC Substrate by MOCVD Method
Seon Jin Mun (National Korea Maritime and Ocean University, South Korea)

S2.04 Properties of thermally phase-changed Ga_2O_3 thin films on p-type Si (100) using MOCVD
Jang Beom An (National Korea Maritime and Ocean University, South Korea)

S2.05 Formation of Ga_2O_3 nanostructures on r-plane sapphire substrates by using of MOCVD
Ji Ye Lee (National Korea Maritime and Ocean University, South Korea)

S2.06 Structural and electric study normally OFF AlGaN/GaN HEMTs with p-type gate
Rafał Kuna (Łukasiewicz PORT, Poland)

S2.07 Influence of precursors on the formation of Ga_2O_3 films grown by mist chemical vapor deposition
Roman Yatskiv (Institute of Photonics and Electronics of CAS, Czech Republic)

S2.08 Monocrystalline GaN Diluted with up to 7.5% Arsenic Grown by MOVPE
Wojciech Olszewski (Łukasiewicz Research Network-PORT, Poland)

S2.09 Growth of quaternary semiconductor crystals CdZnTeSe and CdMnTeSe with differentiated phase component loading
Igor Pritula (Institute For Single Crystals of NASU, Ukraine)

Session S10 - Characterization and Defects in Crystalline Materials

S10.01 Features of the EPR spectra in $Ca_3Y_2(BO_3)_4$:Nd crystal
Igor Pritula (Institute For Single Crystals of NASU, Ukraine)

S10.02 Effect of low-energy beam irradiation on MOCVD-grown GaN layers
František Hájek (Unipress, Poland)

S10.03 Single crystal growth of the high temperature thermoelectrics Ru_2Si_3 and Ru_2Ge_3 by the optical floating zone technique
Jacob Svane (Aarhus University, Denmark)

S10.04 Nanostructure associated properties of $FexBi_2Se_3$ single crystals
Jan Zich (University of Pardubice, Czech Republic)

S10.05 m-line Frank-Shockley partial dislocations in wurtzite GaN: atomistic simulations and electron microscopy observations
Joanna Moneta (Unipress, Poland)

S10.06 Novel implantation-based exfoliation process for β-Ga_2O_3 nanomembrane and microtube fabrication
Katharina Lorenz (University of Lisbon, Portugal)

S10.07 Anisotropic Photoluminescence from Bulk beta-Ga_2O_3 Crystals
Krzysztof Korona (University of Warsaw, Poland)

S10.08 The multi-scale analysis of structural defects in single-crystalline turbine blades
Robert Paszkowski (University of Silesia in Katowice, Poland)

S10.09 The effects of T6-treatment temperature on the tensile properties of Al–Si based alloys
Zakia Sersour (UMMB, Algeria)

S10.10 Luminescence of Bi_3TeBO_9 crystalline ceramics doped with Yb^{3+} and Tm^{3+} ions
Taras Zhezhera (Poznan University of Technology, Poland)

Session S11 - Bulk Crystal Growth

S11.01 Synthesis and characterization of large WO_3 single crystals
Alexander Kunzmann (University of Duisburg-Essen, Germany)

S11.02 The impact of solidification rates on the microstructure and properties of GaSb-Ge eutectic crystals
Ali Abbas (ENSEMBLE^3, Poland)

S11.03 Alkali Boro Phosphate glass rods doped with rare-earth ions and metal nano particles for solid state lighting applications
Govindan Vadivel (ENSEMBLE^3, Poland)

S11.04 Topological insulator eutectic heterostructures
Krzysztof Markus (ENSEMBLE^3, Poland)

S11.05 Optimizing Thermal Profiles and Stability for Growth of Bulk Crystals in the B_2O_3-BaO-Na_2O System
Martynas Misevicius (Center for Physical Sciences and Technology, Lithuania)

S11.06 TSFZ growth of incongruently melting compounds: case of LSCO-based superconducting crystals
Olesia Voloshyna (IFW Dresden, Germany)

S11.07 Smart growth, from combined crystal growth methods to artificial intelligence management: control of the chemical composition and improvement of single crystal performance
Philippe R. Veber (West University Timisoara, Romania)

S11.08 Single Crystal Growth of YAG:Eu^{3+} by the Travelling Solvent Floating Zone Method and its Luminescence Properties
Ramunas Skaudžius (Vilnius University, Lithuania)

S11.09 Phase Diagram and Single Crystal Growth of Li(Nb,Ta)O_3 Solid Solutions
Roberts Blukis (Leibniz-Institut für Kristallzüchtung, Germany)

S11.10 NiTi growth using the micro pulling down method
Timon Sieweke (University of Duisburg-Essen, Germany)

S11.11 Enhanced optical performance of nanoplasmonic cavity glasses
Piotr Piotrowski (ENSEMBLE^3, Poland)